File Number 2339

2-Ampere Silicon P-N-P Power Transistors

Complementary to the D40E Series

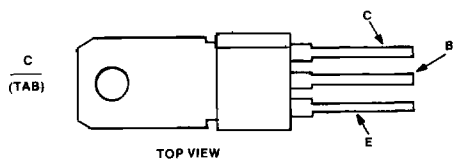
Features:

- High free-air power dissipation
- Low collector saturation voltage (-0.5V typ. @ -1A I_C)
- Excellent linearity
- Fast switching

The D41E-series of silicon p-n-p power transistors are designed for various specific and general purpose applications, such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1 MHz; series, shunt and switching regulators; and low and high frequency inverters/converters.

These devices are supplied in the JEDEC TO-202AB plastic package.

TERMINAL DESIGNATIONS



92CS-43222

JEDEC TO-202AB

MAXIMUM RATINGS (T_A = 25° C) (unless otherwise specified)

RATING	SYMBOL	D41E1	D41E5	D41E7	UNITS
Collector-Emitter Voltage	V_{CEO}	-30	-60	-80	Volts
Collector-Emitter Voltage	V_{CES}	-45	-70	-90	Volts
Emitter Base Voltage	V_{EBO}	-5	-5	-5	Volts
Collector Current — Continuous Peak(1)	I_C I_{CM}	-2 -3	-2 -3	-2 -3	A
Base Current — Continuous	I_B	-1	-1	-1	A
Total Power Dissipation @ T_A = 25°C @ T_C = 25°C	P_D	1.33 8	1.33 8	1.33 8	Watts
Operating and Storage Junction Temperature Range	T_J,T_{stg}	-55 to +150	-55 to +150	-55 to +150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	75	75	75	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	15.6	15.6	15.6	°C/W
Maximum Lead Temperature for Soldering Purposes: ⅛" from Case for 5 Seconds	T_L	+260	+260	+260	°C

(1) Pulse Test Pulse Width = 300ms Duty Cycle ≤ 2%.

ELECTRICAL CHARACTERISTICS (T_C = 25°C) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS(1)						
Collector-Emitter Sustaining Voltage (I_C = -10ma)	D41E1 D41E5 D41E7	$V_{CEO(sus)}$	-30 -60 -80	— — —	— — —	Volts
Collector Cutoff Current (V_{CE} = Rated V_{CES})		I_{CES}	—	—	-0.1	μA
Emitter Cutoff Current (V_{EB} = -5V)		I_{EBO}	—	—	-0.1	μA
SECOND BREAKDOWN						
Second Breakdown with Base Forward Biased		FBSOA	SEE FIGURE 1			
ON CHARACTERISTICS(1)						
DC Current Gain (I_C = -100mA, V_{CE} = -2V) (I_C = -1A, V_{CE} = -2V)		h_{FE} h_{FE}	50 10	— —	— —	—
Collector-Emitter Saturation Voltage (I_C = -1.0A, I_B = -0.1A)		$V_{CE(sat)}$	—	—	-1.0	Volts
Base-Emitter Saturation Voltage (I_C = -1.0mA, I_B = 0.1A)		$V_{BE(sat)}$	—	—	-1.3	Volts
DYNAMIC CHARACTERISTICS						
Collector Capacitance (V_{CB} =10V, f = 1M_{Hz})		C_{CBO}	—	13	—	pF
Current-Gain Bandwidth Product (I_C = -100mA, V_{CE} = -10V)		f_T	—	175	—	MHz
SWITCHING CHARACTERISTICS						
Resistive Load						
Delay Time + Rise Time	I_C = -1A, I_{B1} = I_{B2} = -0.1A	$t_d + t_r$	—	180	—	nS
Storage Time	V_{CC} = -30V, t_p = 25 μsec	t_s	—	250	—	
Fall Time		t_f	—	110	—	

(1) Pulse Test PW = 300ms Duty Cycle ≤ 2%.

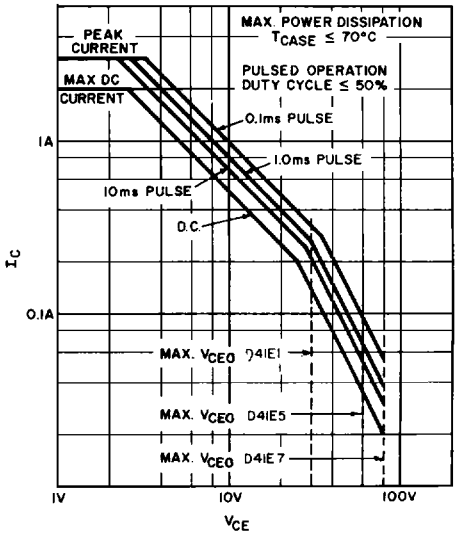


FIG. 1 SAFE REGION OF OPERATION

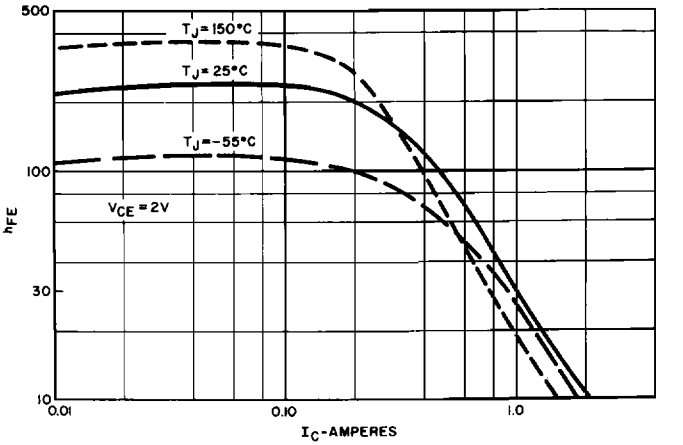


FIG. 2 TYPICAL H_{FE} VS I_C

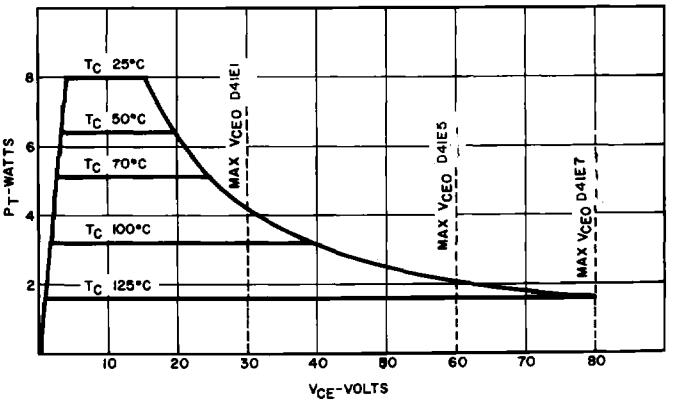


FIG. 3 MAXIMUM PERMISSIBLE DC POWER DISSIPATION

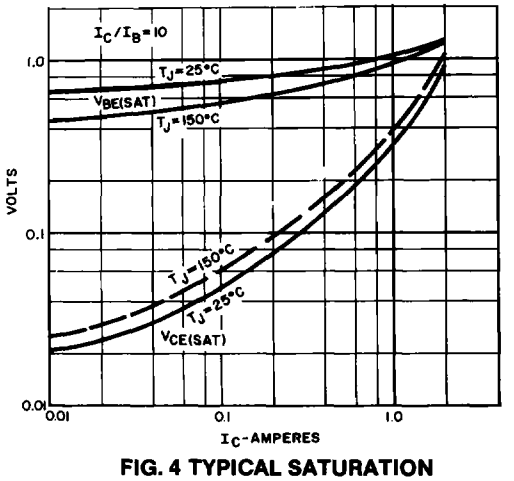


FIG. 4 TYPICAL SATURATION VOLTAGE CHARACTERISTICS

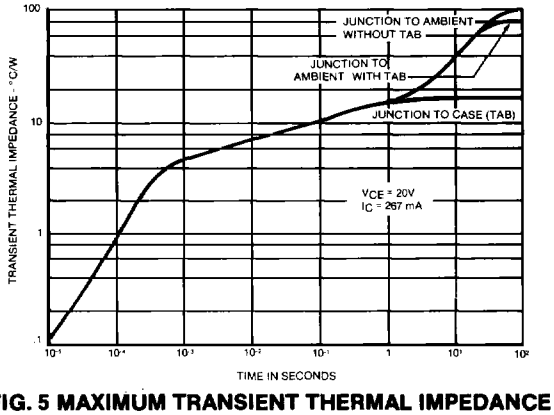


FIG. 5 MAXIMUM TRANSIENT THERMAL IMPEDANCE